

SF₄ as a New Fluorine Reagent for Thermal ALE: Application to Al₂O₃ and VO₂ ALE

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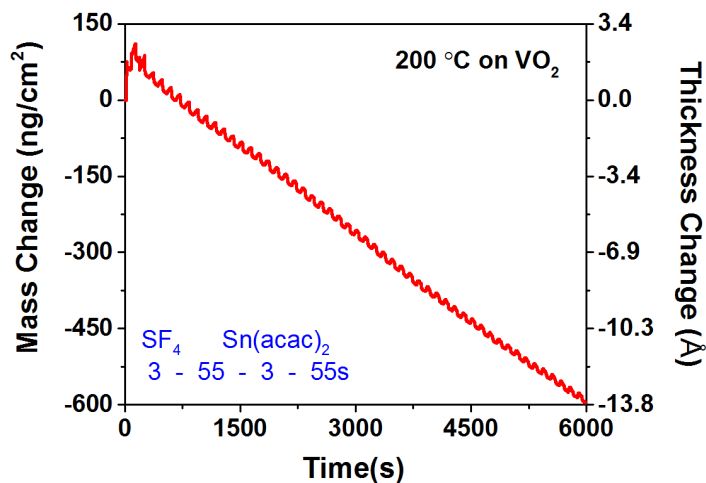


Figure 1. QCM measurements of mass change versus time showing 50 ALE cycles of VO₂ ALE using SF₄ and Sn(acac)₂ as the reactants. The etch rate is ~0.3 Å/cycle.

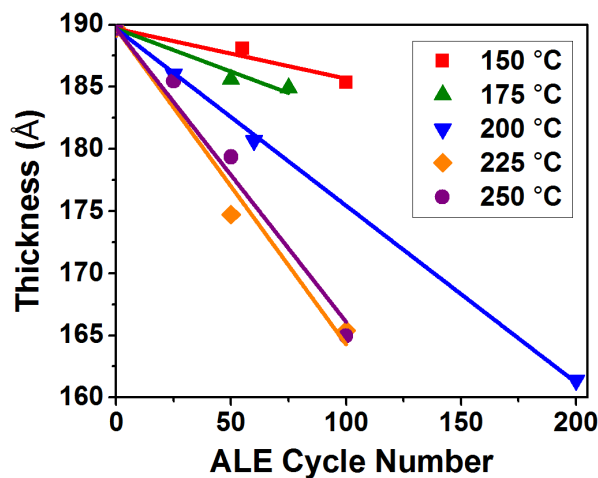


Figure 2. SE measurements of Al₂O₃ film thickness versus ALE cycle number showing temperature dependence of Al₂O₃ ALE using SF₄ and Sn(acac)₂ as the reactants.